nse '

#### **MAXIMUM RATINGS** (T<sub>J</sub> = 25 C unless otherwise noted)

Rating			Value	Unit
Drain-to-Source Voltage Internally Clamped			42	V
Drain-to-Gate Voltage Internally Clamped	$(R_G = 1.0 M\Omega)$	$V_{DGR}$	42	V
Gate-to-Source Voltage		$V_{GS}$	±14	V
Continuous Drain Current			Internally Limited	
Total Power Dissipation	@ T <sub>A</sub> = 25 C (Note 1) @ T <sub>A</sub> = 25 C (Note 2)	P <sub>D</sub>	0.8 1.62	W
Maximum Continuous Drain, both channels on	@ T <sub>A</sub> = 25 C (Note 1) @ T <sub>A</sub> = 25 C (Note 2)	I <sub>D</sub>	1.87 2.65	Α
Thermal Resistance	Junction-to-Ambient Steady State (Note 1) Junction-to-Ambient Steady State (Note 2)	$R_{ hetaJA} \ R_{ hetaJA}$	157 77	C/W
Single Pulse Drain–to–Source Avalanche Energy (V <sub>DD</sub> = 32 V, V <sub>G</sub> = 5.0 V, I <sub>PK</sub> = 1.0 A, L = 300 mH, R <sub>G(ext)</sub> = 25 $\Omega$ )			150	mJ
Load Dump Voltage (V <sub>GS</sub> = 0	np Voltage $(V_{GS} = 0 \text{ and } 10 \text{ V}, R_I = 2.0 \Omega, R_L = 9.0 \Omega, t_d = 400 \text{ ms})$			V
Operating Junction and Storage Temperature			-55 to 150	С

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface—mounted onto min pad FR4 PCB, (Cu area = 40 sq. mm, 1 oz.).

2. Surface—mounted onto 1 sq. FR4 board (Cu area = 625 sq. mm, 2 oz.).

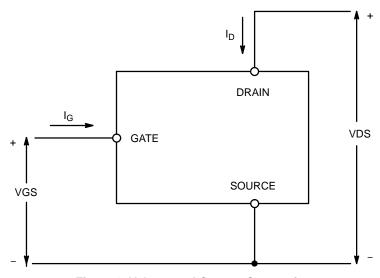


Figure 1. Voltage and Current Convention

Max	Unit	
		•
55	V	
55		
4.0	μΑ	
20		
100	μΑ	
2.2	V	
6.0	-mV/ C	
200	mΩ	
400		
230		
460		
230		
460		
	V	
		•
30	μs	
200	μs	
25	μs	
70	μs	
1.2	V/μs	
0.5		

## **ELECTRICAL CHARACTERISTICS** ( $T_J = 25$ C unless otherwise noted)

Parameter	Test Condition Symbol		Min	Тур	Max	Unit
GATE INPUT CHARACTERISTICS (Note 5)						
Current Limit Gate Input Current	$V_{GS} = 5 \text{ V}, V_{DS} = 10 \text{ V}$	I <sub>GCL</sub>		0.05		mA
	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 10 V	7		0.4		
Thermal Limit Fault Gate Input Current	$V_{GS} = 5 \text{ V}, V_{DS} = 10 \text{ V}$	I <sub>GTL</sub>		0.15		mA
	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 10 V			0.7		

## **TYPICAL PERFORMANCE CURVES**

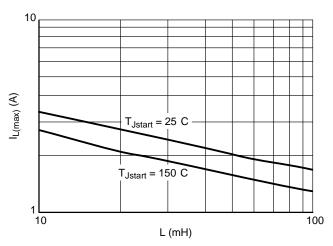
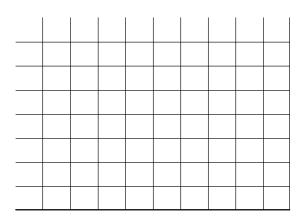
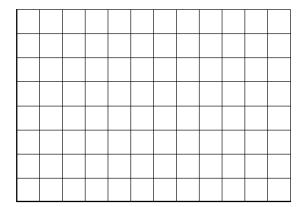


Figure 2. Single Pulse Maximum Switch-off Current vs. Load Inductance



### **TYPICAL PERFORMANCE CURVES**





## **TYPICAL PERFORMANCE CURVES**



Figure 20. Transient Thermal Resistance

## **TEST CIRCUITS AND WAVEFORMS**

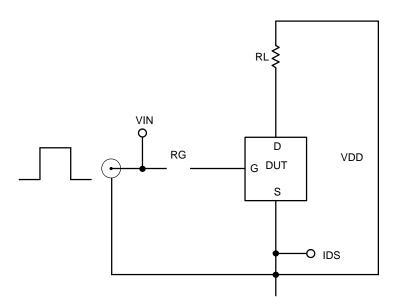


Figure 21. Resistive Load Switching Test Circuit

